



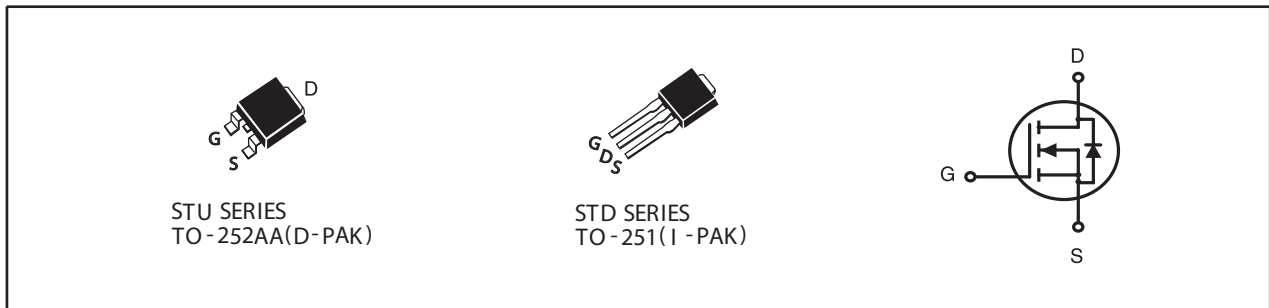
N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

VDSS	ID	RDS(ON) (mΩ) Max
80V	20A	46 @ VGS=10V
		68 @ VGS=4.5V

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- TO-252 and TO-251 Package.



ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous ^a	$T_C=25^\circ\text{C}$	20
		$T_C=70^\circ\text{C}$	16
I_{DM}	-Pulsed ^b	59	A
E_{AS}	Single Pulse Avalanche Energy ^d	64	mJ
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	42
		$T_C=70^\circ\text{C}$	27
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	80			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =64V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{BS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	2	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =10A		37	46	m ohm
		V _{GS} =4.5V , I _D =8.25A		50	68	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =10A		26		S
DYNAMIC CHARACTERISTICS [°]						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		1580		pF
C _{OSS}	Output Capacitance			108		pF
C _{RSS}	Reverse Transfer Capacitance			89		pF
SWITCHING CHARACTERISTICS [°]						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =40V I _D =1A V _{GS} =10V R _{GEN} = 6 ohm		28		ns
t _r	Rise Time			26		ns
t _{D(OFF)}	Turn-Off Delay Time			58		ns
t _f	Fall Time			12		ns
Q _g	Total Gate Charge	V _{DS} =40V, I _D =10A, V _{GS} =10V		25		nC
		V _{DS} =40V, I _D =10A, V _{GS} =4.5V		12.5		nC
Q _{gs}	Gate-Source Charge	V _{DS} =40V, I _D =10A, V _{GS} =10V		2.8		nC
Q _{gd}	Gate-Drain Charge			8.1		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =2A		0.76	1.3	V

Notes

- The maximum current rating is limited by bond-wires.
- Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Starting T_J=25°C, L=0.5mH, V_{DD} = 40V. (See Figure13)

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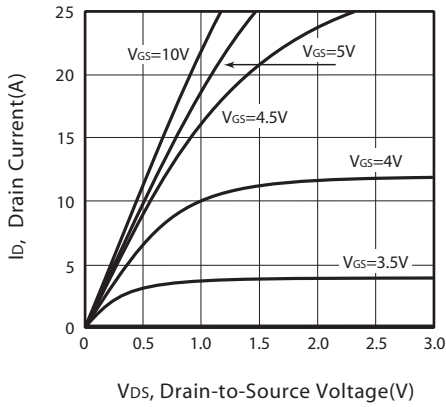


Figure 1. Output Characteristics

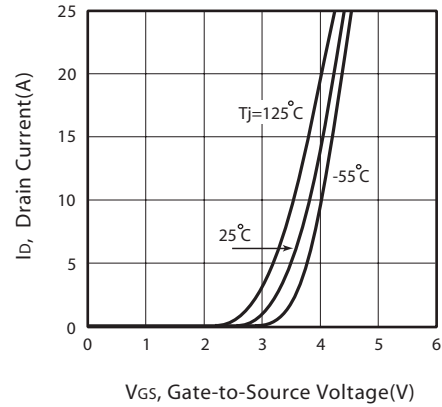


Figure 2. Transfer Characteristics

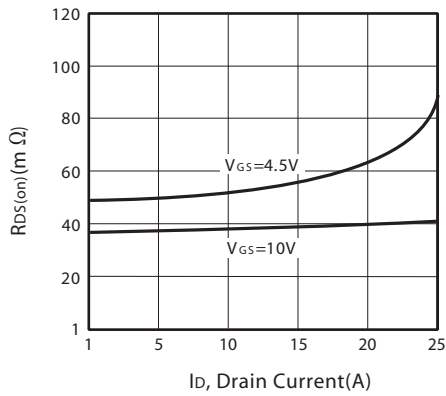


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

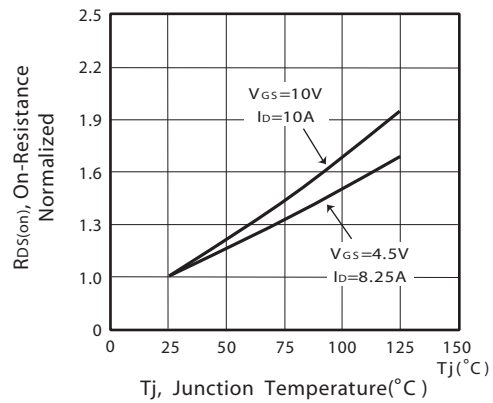


Figure 4. On-Resistance Variation with Drain Current and Temperature

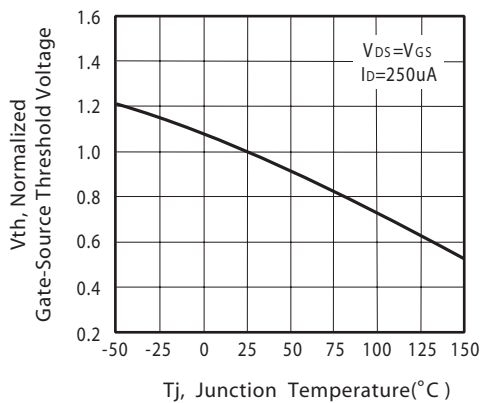


Figure 5. Gate Threshold Variation with Temperature

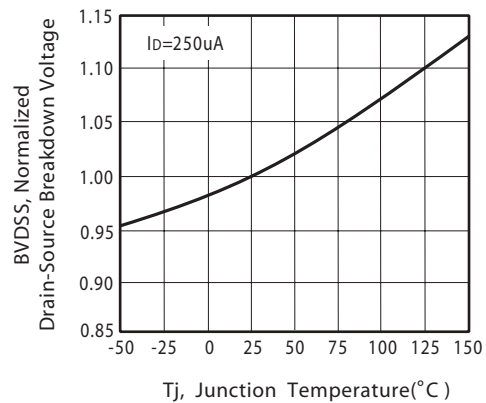


Figure 6. Breakdown Voltage Variation with Temperature

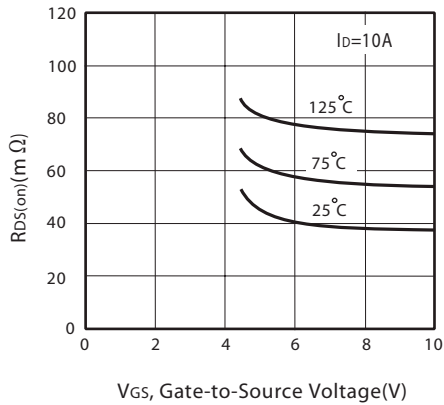


Figure 7. On-Resistance vs. Gate-Source Voltage

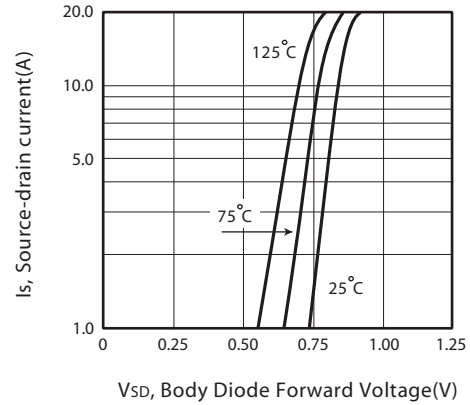


Figure 8. Body Diode Forward Voltage Variation with Source Current

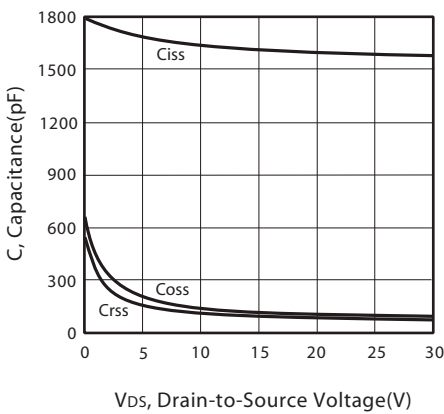


Figure 9. Capacitance

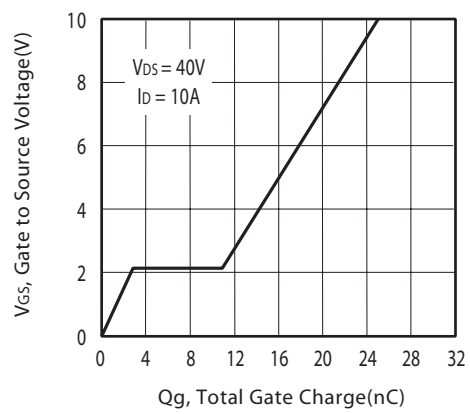


Figure 10. Gate Charge

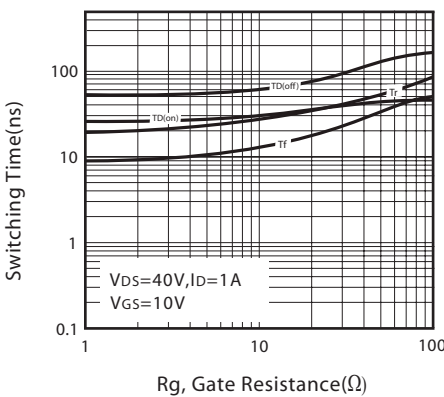


Figure 11. switching characteristics

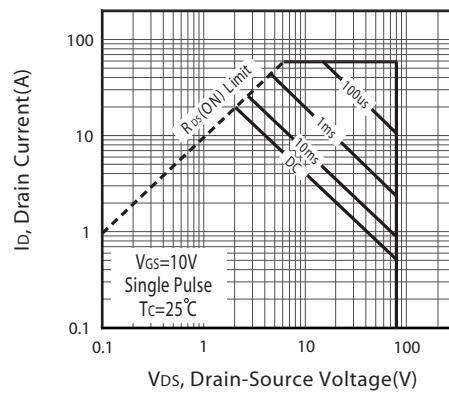
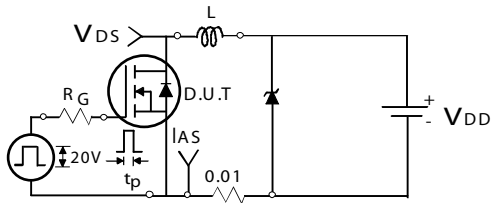
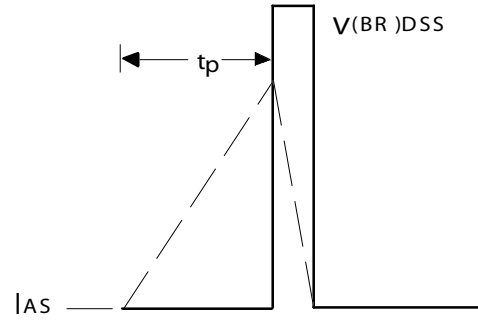


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

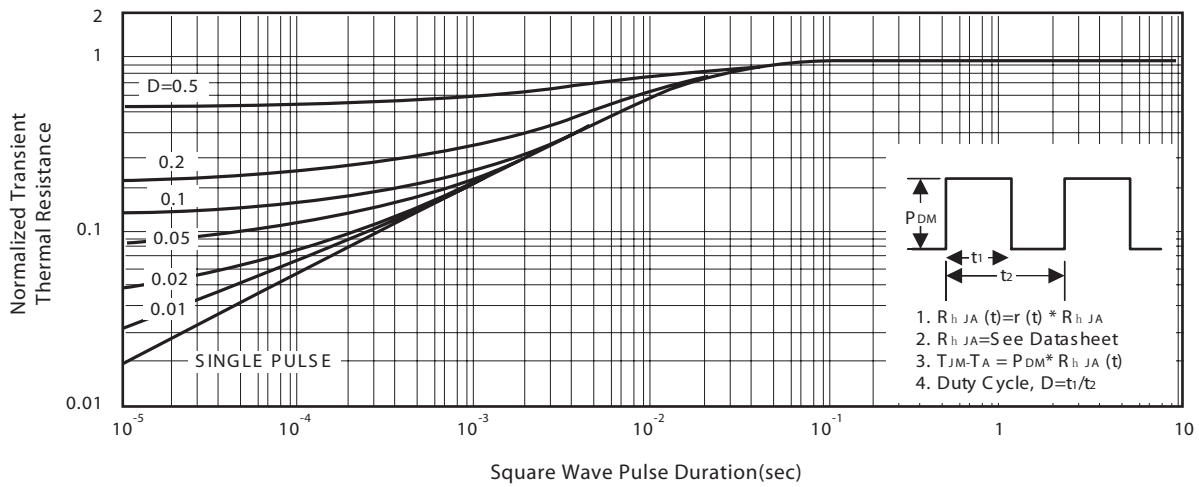
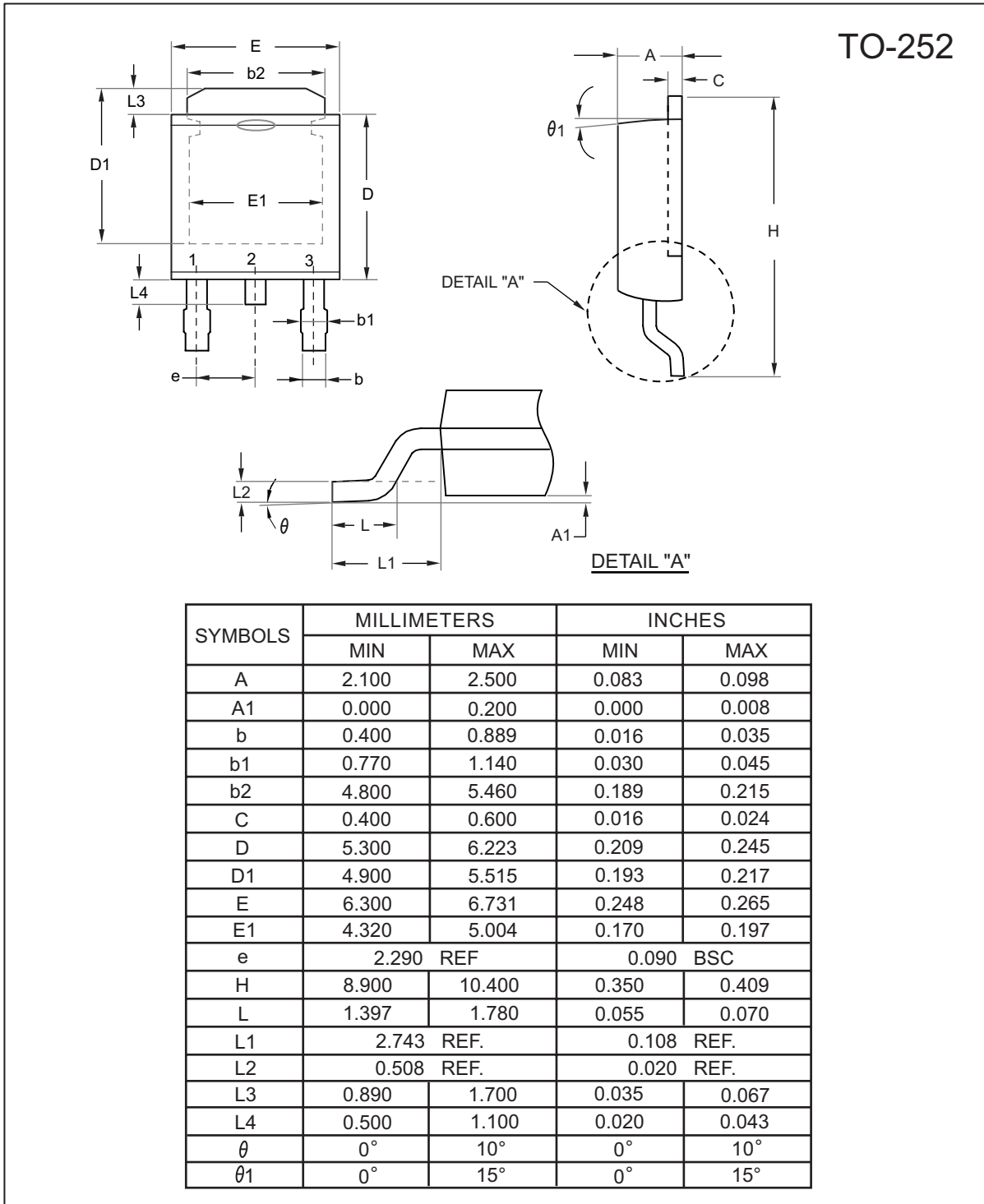


Figure 14. Normalized Thermal Transient Impedance Curve

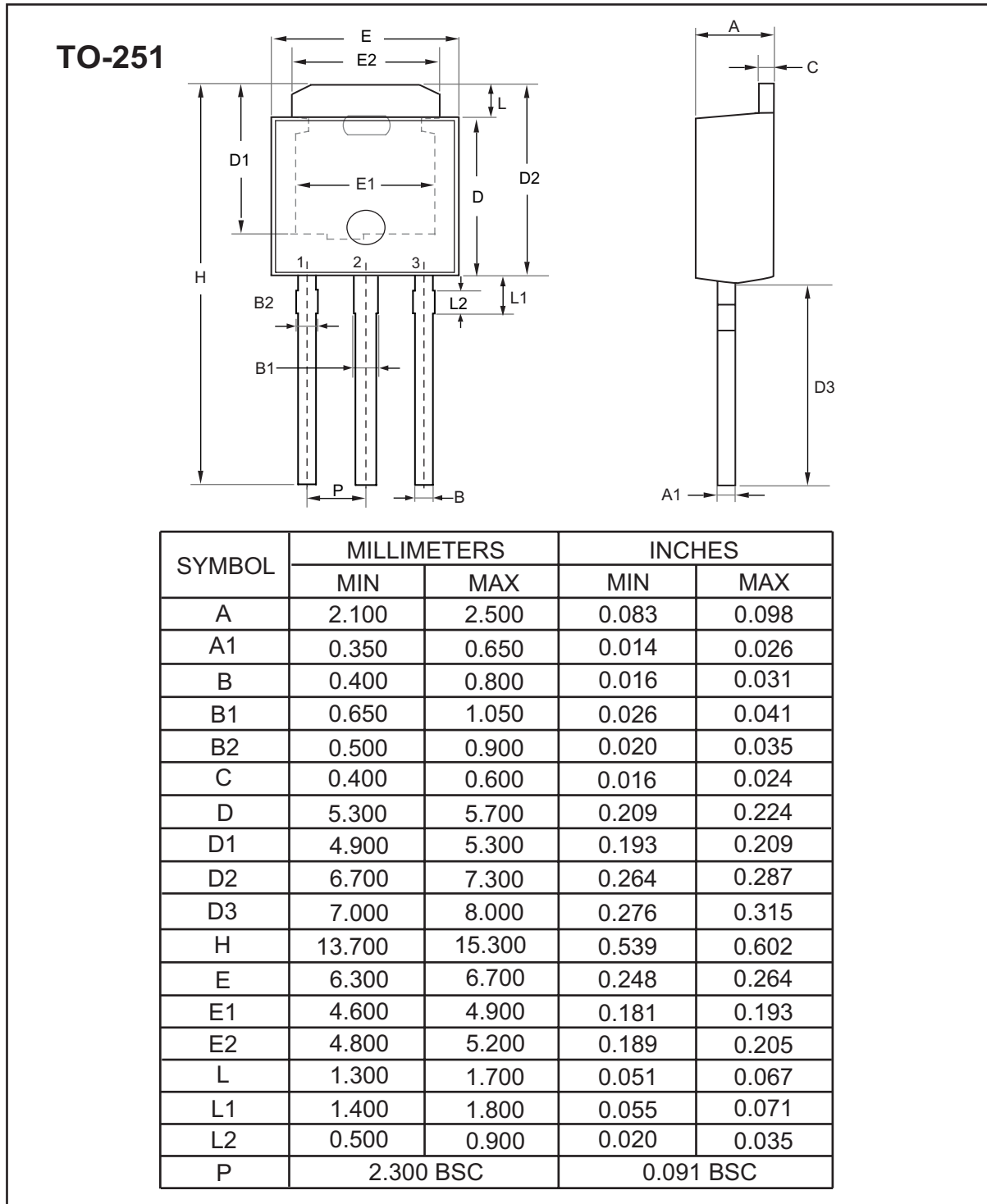
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PACKAGE OUTLINE DIMENSIONS

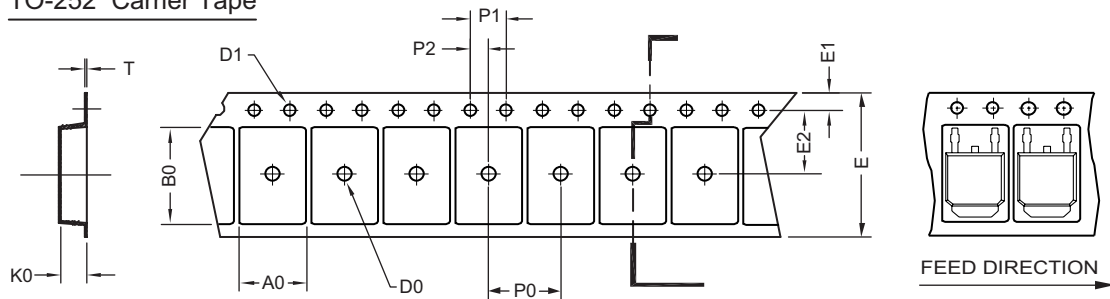


TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



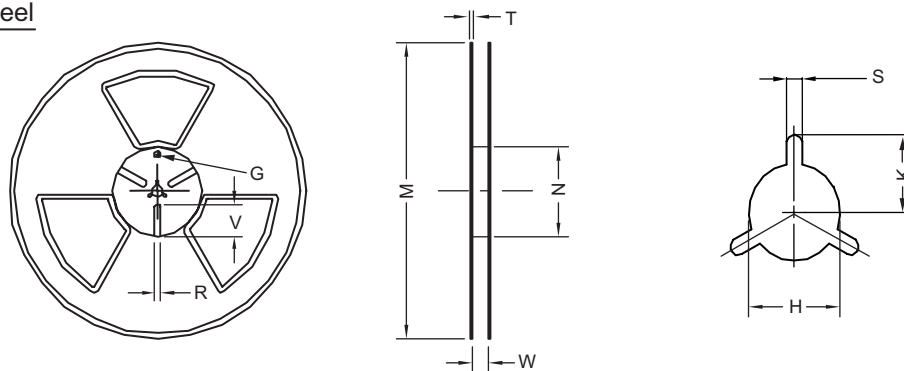
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---